

1 1. A reflector comprising:
2 a reflective layer; and
3 an absorbing layer that preferentially absorbs
4 blue light, said absorbing layer being located over said
5 reflective layer.

1 2. The reflector of claim 1 wherein said reflector
2 is a micromirror.

1 3. The reflector of claim 1 wherein said reflective
2 layer is formed of silver, said silver being formed over a
3 polished semiconductor material.

1 4. The reflector of claim 3 wherein said silver
2 layer is covered by an insulator.

1 5. The reflector of claim 3 wherein the absorbing
2 layer includes silicon nitride.

1 6. The reflector of claim 4 wherein said absorbing
2 layer includes silicon dioxide.

1 7. The reflector of claim 4 wherein said insulator
2 includes about 700 to 750 Angstroms of silicon dioxide and
3 about 700 to about 750 Angstroms of silicon nitride.

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1 8. A method comprising:
2 forming a reflective layer; and
3 forming an absorbing layer over said reflective
4 layer that absorbs a particular wavelength of light.

1 9. The method of claim 8 including forming a
2 reflective layer by depositing silver on a semiconductor
3 layer.

1 10. The method of claim 8 including forming an
2 absorbing layer including a layer of two different
3 insulator materials.

1 11. The method of claim 9 including forming said
2 silver layer at a temperature of 50°C or less.

1 12. The method of claim 10 including forming said
2 absorbing layer at a temperature of less than 250°C.

1 13. The method of claim 12 including forming said
2 absorbing layer using chemical vapor deposition.

1 14. The method of claim 8 including forming said
2 absorbing layer of a layer of oxide and a layer of nitride.

1 15. The method of claim 14 including forming said
2 oxide and nitride layers of a thickness of about 700 to
3 about 750 Angstroms.

1 16. A reflector comprising:
2 a silicon substrate; and
3 a silver layer formed directly on said silicon
4 substrate.

1 17. The reflector of claim 16 wherein said reflector
2 is a micromirror.

1 18. The reflector of claim 16 including an absorbing
2 layer over said silver layer.

1 19. The reflector of claim 18 wherein said absorbing
2 layer preferentially absorbs blue light.

1 20. The reflector of claim 18 wherein said absorbing
2 layer includes silicon nitride.

1 21. The reflector of claim 20 wherein said absorbing
2 layer includes silicon dioxide.

1 22. The reflector of claim 21 wherein said insulator
2 includes about 700 to 750 Angstroms of silicon dioxide and
3 from about 700 to about 750 Angstroms of silicon nitride.

1 23. The reflector of claim 16 wherein said silver
2 layer is formed at a temperature below 50°C.

1 24. The reflector of claim 18 wherein said insulator
2 is formed at a temperature below 250°C.

1 25. A method comprising:
2 depositing silver on a silicon substrate at a
3 temperature less than 50°C; and
4 forming an absorbing layer over said silver.

1 26. The method of claim 25 including forming an
2 absorbing layer including a layer of two different
3 insulator materials.

1 27. The method of claim 26 including forming said
2 absorbing layer at a temperature of less than 250°C.

1 28. The method of claim 26 including forming said
2 absorbing layer of a layer of oxide and a layer of nitride.

1 29. The method of claim 28 including forming said
2 oxide and nitride layers of a thickness of about 700 to
3 about 750 Angstroms.

1 30. The method of claim 25 including depositing
2 silver using chemical vapor deposition.

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